

Form PTO-1449
(MODIFIED)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.

039153-0256 (F0113)

SERIAL NO.

09/599,141

INFORMATION DISCLOSURE CITATION

SEP 04 2003

(Use several sheets if necessary)

APPLICANT

Yu

FILING DATE

06/22/2000

GROUP ART UNIT

2812

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
AR	A1	6,461,945	10/8/2002	Yu			
	A2	6,350,311	2/26/2002	Chin et al.			
	A3	6,319,799	11/20/2001	Ouyang et al.			
	A4	6,310,367	10/30/2001	Yagishita et al.			
	A5	6,268,640	7/31/2001	Park, et al.			
	A6	6,232,622	5/15/2001	Hamada			
	A7	6,190,975	2/20/2001	Kubo et al.			
	A8	6,172,381	1/9/2001	Gardner et al.			
	A9	6,133,082	10/17/2000	Masuoka			
	A10	6,130,144	10/10/2000	Verret			
	A11	6,031,269	2/29/2000	Liu			
	A12	6,022,785	2/8/2000	Yeh, et al.			
	A13	5,985,703	11/16/1999	Banerjee			
	A14	5,981,345	11/9/1999	Ryum, et al.			
	A15	5,936,280	8/10/1999	Liu			
	A16	5,910,015	6/8/1999	Sameshima, et al.			
	A17	5,856,225	01/5/1999	Lee et al.			
	A18	5,821,149	10/13/1998	Schuppen et al.			
	A19	5,766,989	6/16/1998	Maegawa et al.			
	A20	5,753,541	5/19/1998	Shimizu			
	A21	5,689,136	11/18/1997	Usami et al.			
	A22	5,683,934	11/4/1997	Candelaria			
	A23	5,675,185	10/7/1997	Chen et al.			
	A24	5,612,552	3/18/1997	Owens			
	A25	5,591,653	1/7/1997	Sameshima, et al.			
	A26	5,581,101	12/3/1996	Ning et al.			
AR	A27	5,554,870	9/10/1996	Fitch et al.			

EXAMINER

DATE CONSIDERED

- * EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include any copy of this form with next communication to applicant.

Form PTO-1449 (MODIFIED)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 039153-0256 (F0113)	SERIAL NO. 09/599,141
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)		APPLICANT Yu	
		FILING DATE 06/22/2000	GROUP ART UNIT 2812

U.S. PATENT DOCUMENTS

AR	A28	5,497,019	3/5/1996	Mayer et al.			
	A29	5,482,877	1/9/1996	Rhee			
	A30	5,461,250	10/24/1995	Burghartz et al.			
	A31	5,451,798	9/19/1995	Tsuda et al.			
	A32	5,420,048	5/30/1995	Kondo			
	A33	5,414,288	5/9/1995	Fitch et al.			
	A34	5,346,834	9/13/1994	Hisamoto et al.			
	A35	5,321,286	6/14/1994	Koyama et al.			
	A36	5,155,571	10/13/1992	Wang et al.			
	A37	5,128,732	7/7/1992	Sugahara et al.			
	A38	5,041,884	8/20/1991	Kumamoto et al.			
	A39	5,036,374	7/30/1991	Shimbo			
	A40	5,019,882	5/28/1991	Solomon et al.			
	A41	5,008,211	5/16/1991	Yamazaki			
	A42	4,996,574	2/26/1991	Shirasaki			
	A43	4,994,866	2/19/1991	Awano			
	A44	4,975,387	12/4/1990	Prokes et al.			
	A45	4,849,033	7/18/1989	Vander Sande et al.			
	A46	4,710,478	12/1/1987	Yoder et al.			
	A47	4,697,333	10/6/1987	Nakahara			
	A48	4,381,201	4/26/1983	Sakurai			
	A49	4,272,880	6/16/1981	Pashley			
	A50	4,174,521	11/13/1979	Neale			
AR	A51	4,046,618	9/6/1977	Chaudhari et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO
AR	A52	JP-5-335482	12/1993	Japan				✓
	A53	EP 0 334 682-A2	03/1989	European				
	A54	3-288471	12/18/1991	Japan				✓
AR	A55	61-180466	8/13/1986	Japan				✓

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AR	A56	"Smart-Cut: The Basic Fabrication Process for UNIBOND Soi Wafers" Herve, et al., March 3, 1997.
----	-----	---

12/23/03

Form PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 039153-0256 (F0113)	SERIAL NO. 09/599,141
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				APPLICANT Yu	
				FILING DATE 06/22/2000	
GROUP ART UNIT 2812					
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
AR	A56	"Sub-100nm Gate Length Metal Gate NMOS Transistors Fabricated by a Replacement Gate Process" By Chatterjee, December 7-10, 1997 IEEE.			
AR	A58	U.S. Patent Application Serial No. 09/599,270 entitled "A SOLID PHASE EPITAXY PROCESS FOR MANUFACTURING TRANSISTOR SHAVING SILICON/GERMANIUM CHANNEL REGIONS" by Yu on 6/22/00. (Atty. Dkt. No. 39153-268)			
AR	A59	U.S. Patent Application Serial No. 09/817,580 entitled "METHOD OF LOCALLY FORMING A SILICON/GERMANIUM CHANNEL LAYER" by Yu on 03/26/2001. (Atty. Dkt. No. 39153-428)			
EXAMINER <i>[Signature]</i>					
DATE CONSIDERED 12/23/03					
* EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include any copy of this form with next communication to applicant.					

RECEIVED
SEP -9 2003
TECHNOLOGY CENTER-2800